

• General Description

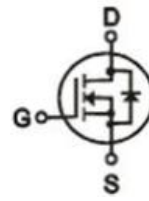
The ZM130N04U combines trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$. This device is ideal for load switch and battery protection applications.

• Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

• Application

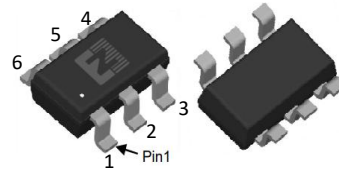
- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

• Product Summary


$V_{DS}=40V$

$R_{DS(ON)} = 13m\Omega$

$I_D=8A$


SOT23-6
• Ordering Information:

Part NO.	ZM130N04U
Marking	130N04
Packing Information	REEL TAPE
Basic ordering unit (pcs)	3000

• Absolute Maximum Ratings (T_C =25°C)

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	V_{DS}	40	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current ^②	$I_{D@TC=25^{\circ}C}$	8	A
	$I_{D@TC=75^{\circ}C}$	6	A
	$I_{D@TC=100^{\circ}C}$	5	A
Pulsed Drain Current ^①	I_{DM}	18	A
Total Power Dissipation ^②	$P_{D@TC=25^{\circ}C}$	2.1	W
Total Power Dissipation	$P_{D@TA=25^{\circ}C}$	1.25	W
Operating Junction Temperature	T_J	-55 to 150	°C
Storage Temperature	T_{STG}	-55 to 150	°C

•Thermal resistance

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal resistance, junction - case ^②	R _{thJC}	-	-	60	°C/W
Thermal resistance, junction - ambient	R _{thJA}	-	-	100	°C/W
Soldering temperature, wavesoldering for 10s	T _{sold}	-	-	265	°C

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	40			V
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	1.2		2.5	V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =40V, V _{GS} =0V			1.0	uA
Gate- Source Leakage Current	I _{GSS}	V _{GS} =±20V, V _{DS} =0V			±100	nA
Static Drain-source On Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =8A		13	17	mΩ
		V _{GS} =4.5V, I _D =6A		16	21	mΩ
Forward Transconductance	g _{FS}	V _{DS} =10V, I _D =5A		12		s
Source-drain voltage	V _{SD}	I _S =8A			1.28	V

•Electronic Characteristics

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Input capacitance	C _{iSS}	f = 1MHz V _{DS} =25V	-	1150	-	pF
Output capacitance	C _{oss}		-	290	-	
Reverse transfer capacitance	C _{rSS}		-	200	-	

•Gate Charge characteristics(Ta= 25°C)

Parameter	Symbol	Condition	Min.	Typ	Max.	Unit
Total gate charge	Q _g	V _{DD} =25V	-	15	-	nC
Gate - Source charge	Q _{gs}	I _D = 8A	-	6	-	
Gate - Drain charge	Q _{gd}	V _{GS} = 10V	-	8	-	

Note: ① Pulse Test : Pulse width ≤ 300μs, Duty cycle ≤ 2% ;

② Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate;

Fig.1 Power Dissipation Derating Curve

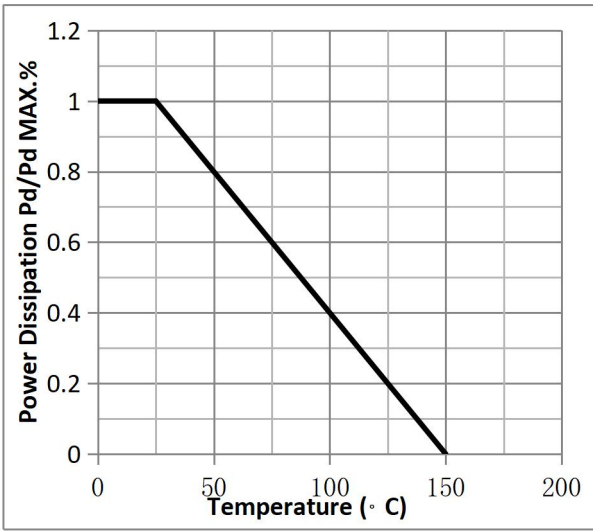


Fig.2 Typical output Characteristics

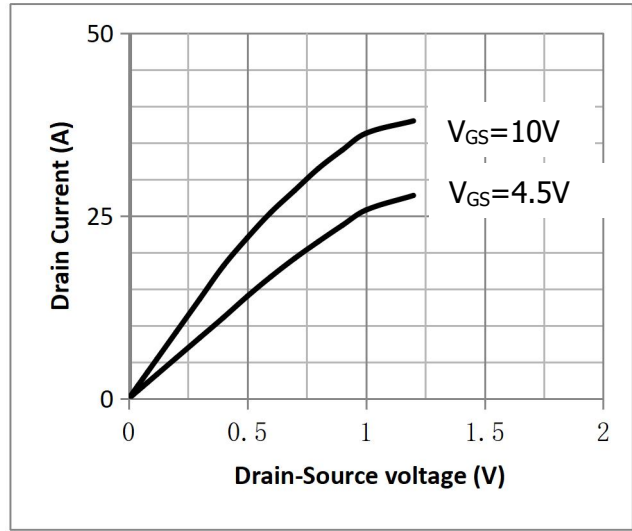


Fig.3 Threshold Voltage V.S Junction Temperature

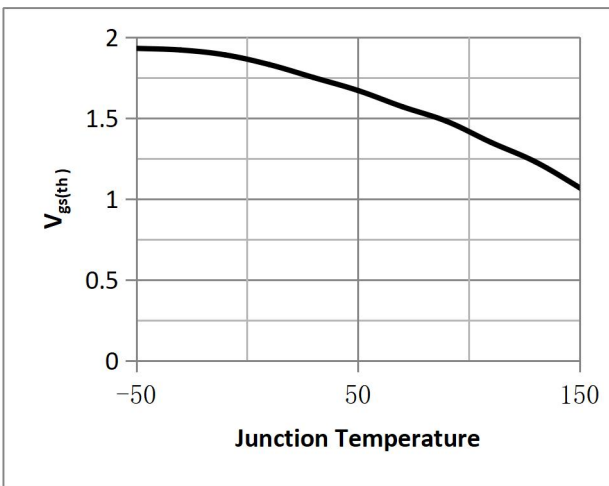


Fig.4 Resistance V.S Drain Current

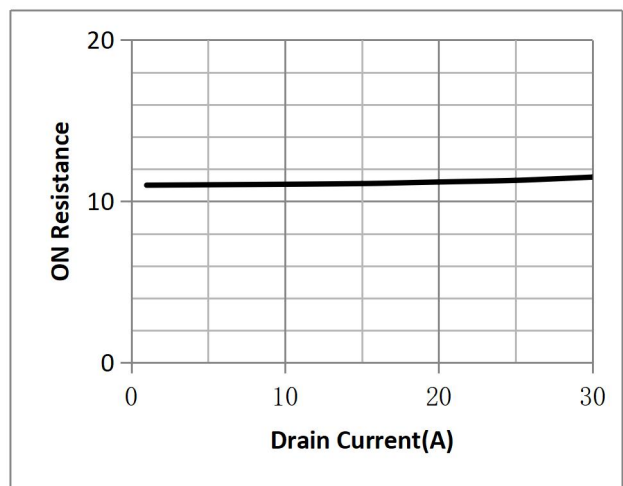


Fig.5 On-Resistance VS Gate Source Voltage

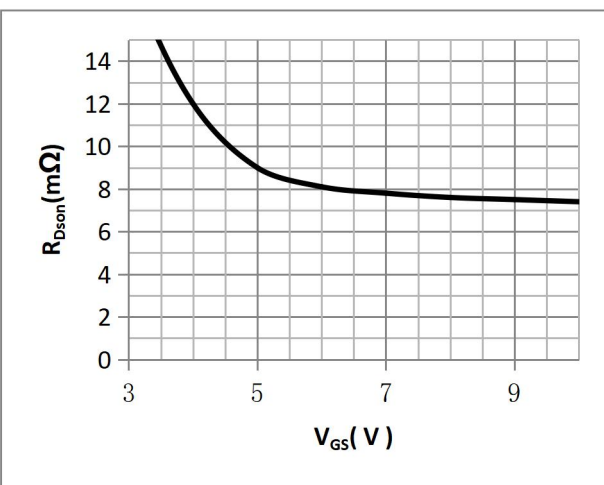


Fig.6 On-Resistance V.S Junction Temperature

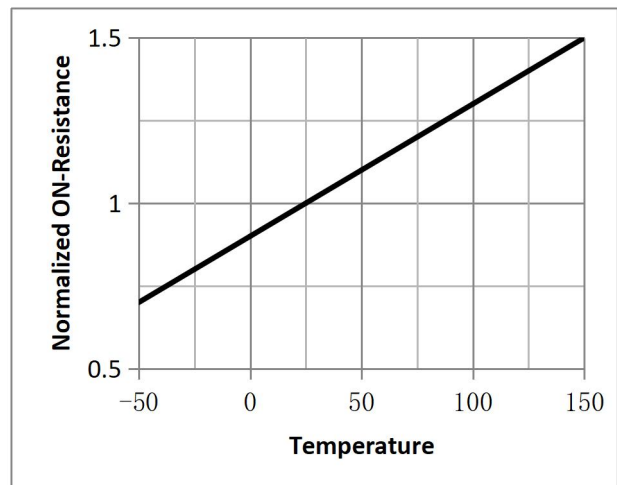


Fig.7 Switching Time Measurement Circuit

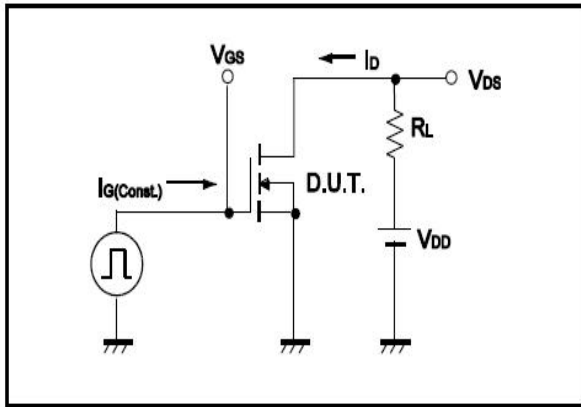


Fig.8 Gate Charge Waveform

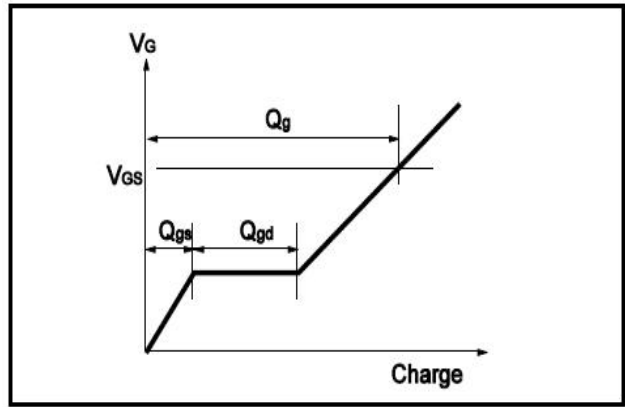


Fig.9 Switching Time Measurement Circuit

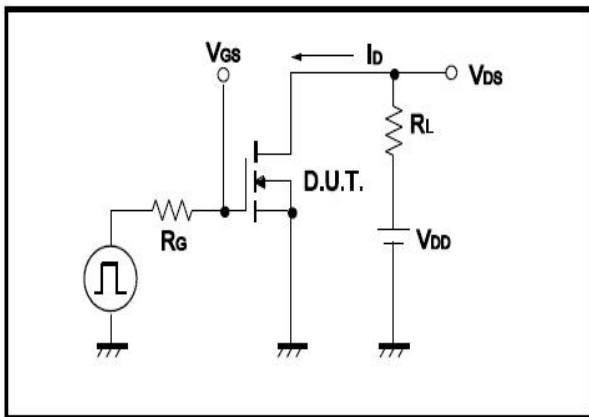


Fig.10 Gate Charge Waveform

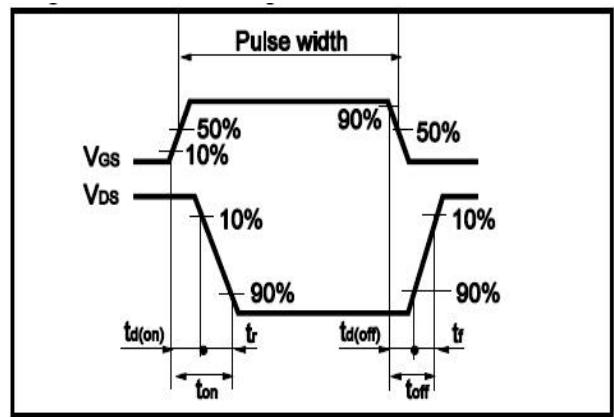


Fig.11 Avalanche Measurement Circuit

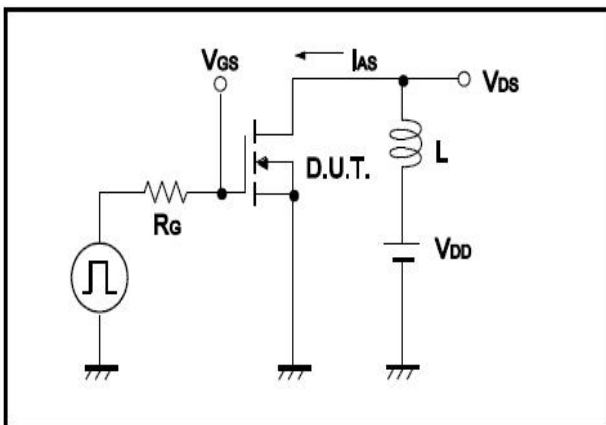
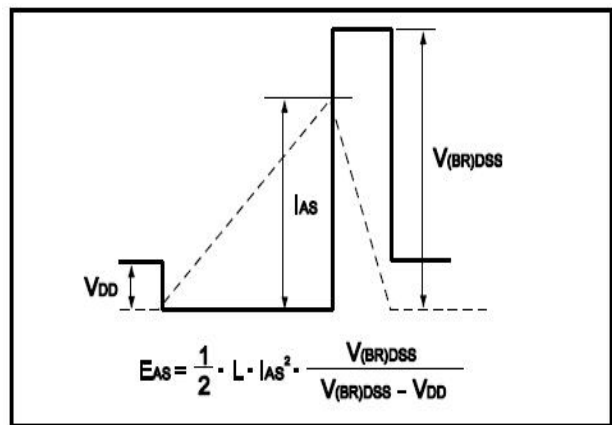


Fig.12 Avalanche Waveform



•Dimensions(SOT23-6)

Unit: mm

